WHAT IS CLAIMED IS:

1. A beam adjusting method comprising:

applying a beam onto a beam adjusting sample having a flat surface being like a plate and having two edges orthogonal to each other; and

detecting the amount of beam passing through the beam adjusting sample;

wherein the beam vertically scans the two edges.

2. The beam adjusting method according to claim 1, wherein the beam adjusting sample is defined by the two edges, and has a through hole penetrating in a thickness direction, and the beam has a scan direction changed over the through hole.

3. The beam adjusting method according to claim 1, wherein the two edges of the beam adjusting sample are two edges at the end portion of the beam adjusting sample, and the beam has the scan direction changed over the beam adjusting sample or outside the beam adjusting sample.

4. The beam adjusting method according to claim 1, wherein the beam is adjusted on the basis of an applied position of the beam and the amount of beam.

5. The beam adjusting method according to claim 1, further comprising applying the beam onto a microstructure placed on the beam adjusting sample to adjust a beam applying direction.

6. The beam adjusting method according to claim 1,

further comprising detecting the height position of the beam adjusting sample.

7. A beam adjusting sample including a flat surface being like a plate and has two edges orthogonal to each other.

8. The beam adjusting sample according to claim 7, wherein the beam adjusting sample is defined by the two edges, and has a through hole penetrating in a thickness direction.

9. The beam adjusting sample according to claim 7, wherein the two edges are two edges at the beam adjusting sample end.

10. The beam adjusting sample according to claim 6, wherein a microstructure is attached on the surface of the beam adjusting sample.

11. The beam adjusting sample according to claim 10, wherein a film of an element having a high electron stopping power is coated on the surface of the microstructure.

12. A beam adjusting device comprising:

a stage for laying a beam adjusting sample having a flat surface being like a plate and having two edges orthogonal to each other;

a beam generator for applying a beam onto the beam adjusting sample;

a secondary electron detector for detecting a secondary electron generated by applying the beam;

a position detector for detecting the position of the

beam adjusting sample; and

a beam detector disposed under the stage,

wherein the beam detector detects an amount of electron beam passing through the beam adjusting sample.

13. The beam adjusting device according to claim 12, wherein the beam adjusting sample is defined by the two edges, and has a through hole penetrating in a thickness direction, and the beam generator applies the electron beam to have a scan direction changed over the through hole.

14. The beam adjusting device according to claim 12, wherein the two edges of the beam adjusting sample are two edges at the end of the beam adjusting sample, and the beam generator applies the beam to have the scan direction changed over the beam adjusting sample or outside the beam adjusting sample.

15. The beam adjusting device according to claim 12, wherein the beam generator applies the beam onto a microstructure placed on the surface of the beam adjusting sample.

16. The beam adjusting device according to claim 15, wherein a film of an element having a high electron stopping power is coated on the surface of the microstructure.